

IN THE CLAIMS

Please amend the claims as follows:

1-10. Canceled.

11. (Original.) A method for making a semiconductor device comprising:

- forming a first dielectric layer on a substrate;

- forming a polysilicon containing layer on the first dielectric layer;

- forming a first silicon nitride layer on the polysilicon containing layer;

- forming an etch stop layer on the first silicon nitride layer;

- etching the etch stop layer, the first silicon nitride layer, the polysilicon containing layer, and the first dielectric layer, to form a patterned etch stop layer, a patterned first silicon nitride layer, a patterned polysilicon containing layer, and a patterned first dielectric layer;

- depositing a second silicon nitride layer on the substrate, the patterned etch stop layer, and on opposite sides of the patterned polysilicon containing layer;

- removing the second silicon nitride layer from part of the substrate and from the patterned etch stop layer to form first and second spacers on opposite sides of the patterned polysilicon containing layer;

- forming source and drain regions that comprise a silicide next to the first and second spacers;

- forming a second dielectric layer on the patterned etch stop layer and on the substrate;

- removing the second dielectric layer from the patterned etch stop layer;

- removing the patterned etch stop layer from the patterned first silicon nitride layer;

- removing the patterned first silicon nitride layer from the patterned polysilicon containing layer;

- removing the patterned polysilicon containing layer to generate a trench

that is positioned between the first and second spacers; and
filling at least part of the trench with a metal layer.

12-14. Canceled.

15. (Original.) The method of claim 11 wherein:
the first dielectric layer is between about 5 and about 20 angstroms thick;
the polysilicon containing layer is between about 100 and about 2,000
angstroms thick;
the first silicon nitride layer is between about 100 and about 500 angstroms
thick;
the etch stop layer is between about 200 and about 1,200 angstroms
thick; and
the metal layer serves as a workfunction metal that fills only part of the
trench and is between about 50 and about 1,000 angstroms thick; and
further comprising depositing on the metal layer a trench fill material.

16-20. Canceled.